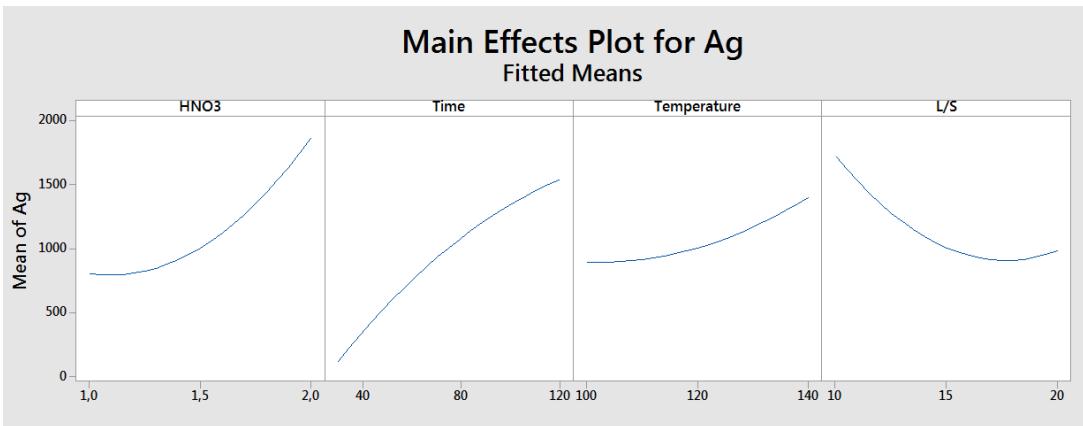
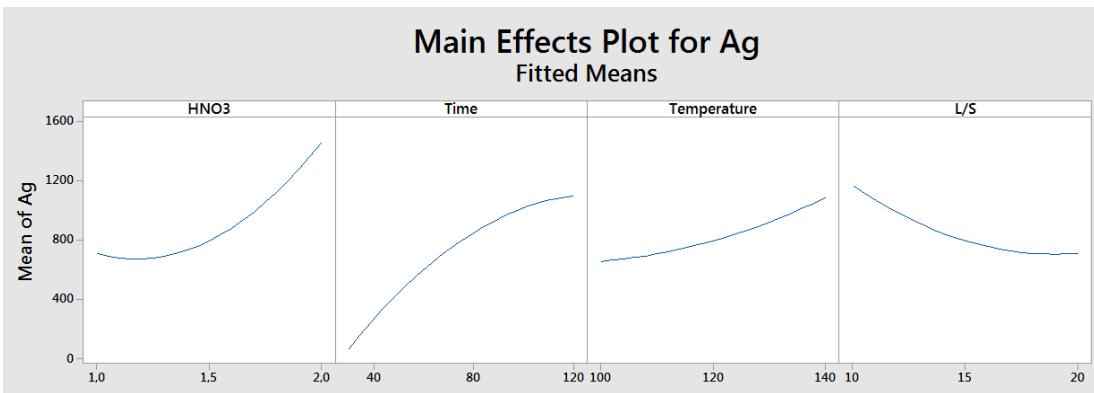


Table S1. Analysis of Variance of the model (Response surface methodology with a Box- Behnken design) for Ag leaching from (a) m-Si and (b) p-Si waste panel.

(a)Analysis of Variance (m-Si)	DF	Adj SS	Adj MS	F-Value	P-Value
Model	14	15647933	1117709	4,20	0,009
Linear	4	11730171	2932543	11,01	0,001
HNO3	1	3326842	3326842	12,49	0,004
Time	1	6014084	6014084	22,58	0,000
Temperature	1	765697	765697	2,87	0,116
L/S	1	1623548	1623548	6,09	0,030
Square	4	1678834	419709	1,58	0,244
HNO3*HNO3	1	567900	567900	2,13	0,170
Time*Time	1	170053	170053	0,64	0,440
Temperature*Temperature	1	105658	105658	0,40	0,541
L/S*L/S	1	631262	631262	2,37	0,150
2-Way Interaction	6	2238927	373155	1,40	0,291
HNO3*Time	1	562021	562021	2,11	0,172
HNO3*Temperature	1	48457	48457	0,18	0,677
HNO3*L/S	1	353885	353885	1,33	0,272
Time*Temperature	1	748129	748129	2,81	0,120
Time*L/S	1	511250	511250	1,92	0,191
Temperature*L/S	1	15184	15184	0,06	0,815
Error	12	3196596	266383		
Lack-of-Fit	10	1565594	156559	0,19	0,972
(b)Analysis of Variance (p-Si)	DF	Adj SS	Adj MS	F-Value	P-Value
Model	14	8625209	616086	5,1	0,004
Linear	4	6024329	1506082	12,48	0
HNO3	1	1668330	1668330	13,82	0,003
Time	1	3189906	3189906	26,42	0
Temperature	1	552595	552595	4,58	0,054
L/S	1	613498	613498	5,08	0,044
Square	4	1114108	278527	2,31	0,118
HNO3*HNO3	1	444487	444487	3,68	0,079
Time*Time	1	236774	236774	1,96	0,187
Temperature*Temperature	1	31579	31579	0,26	0,618
L/S*L/S	1	108665	108665	0,9	0,361
2-Way Interaction	6	1486771	247795	2,05	0,136
HNO3*Time	1	193108	193108	1,6	0,23
HNO3*Temperature	1	152028	152028	1,26	0,284
HNO3*L/S	1	335452	335452	2,78	0,121
Time*Temperature	1	315618	315618	2,61	0,132
Time*L/S	1	171747	171747	1,42	0,256
Temperature*L/S	1	318818	318818	2,64	0,13
Error	12	1448598	120716		
Lack-of-Fit	10	739026	73903	0,21	0,965
Pure Error	2	709571	354786		
Total	26	10073806			



(a) m-Si panel



(b) p-Si panel

Figure. S1. The main effects plot for the parameters HNO₃, Time, Temperature and S/L ratio on Ag leaching from (a) m-Si and (b) p-Si waste panel.

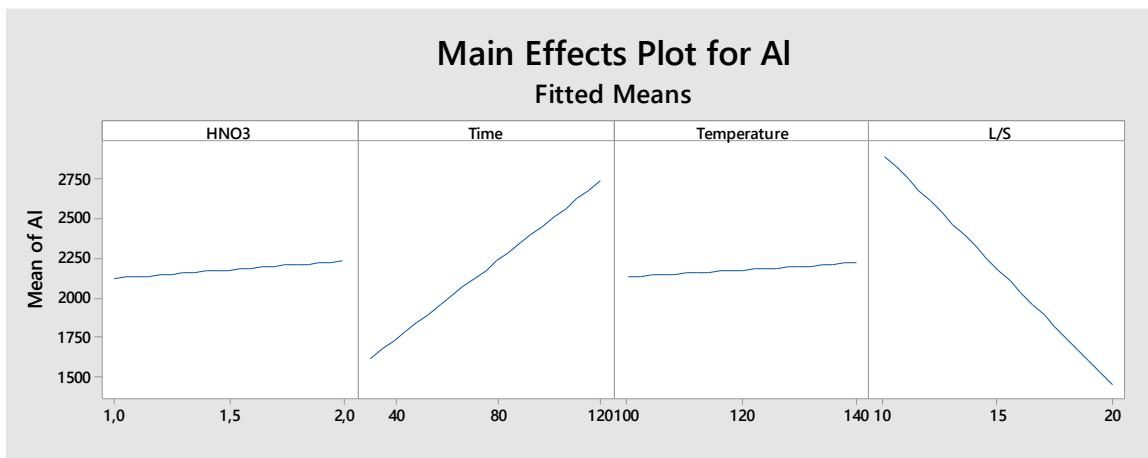


Figure. S2. The main effects plot for the parameters HNO₃, Time, Temperature and S/L ratio on Al leaching from m-Si waste panel.

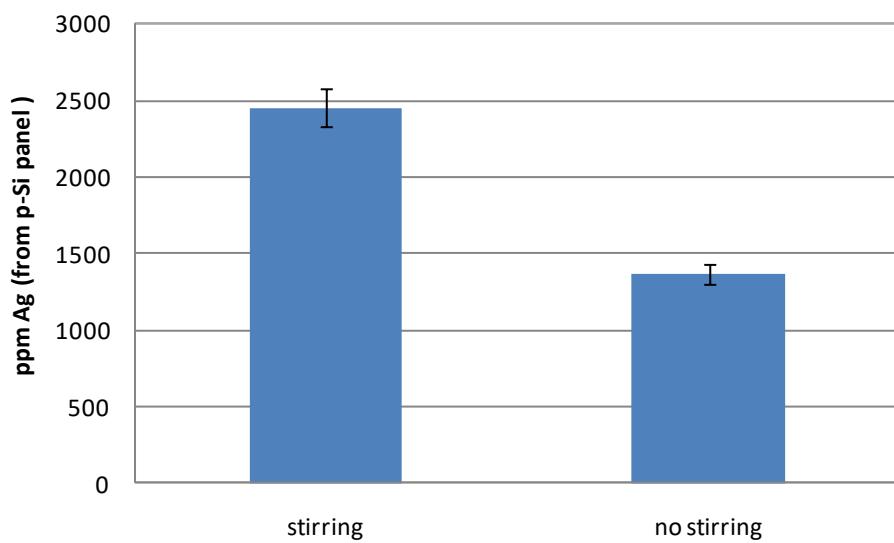


Figure. S3. The effect of stirring on Ag leaching (p-Si panel, HNO₃ 2N, S/L=1/10, 2 h, 45 °C).

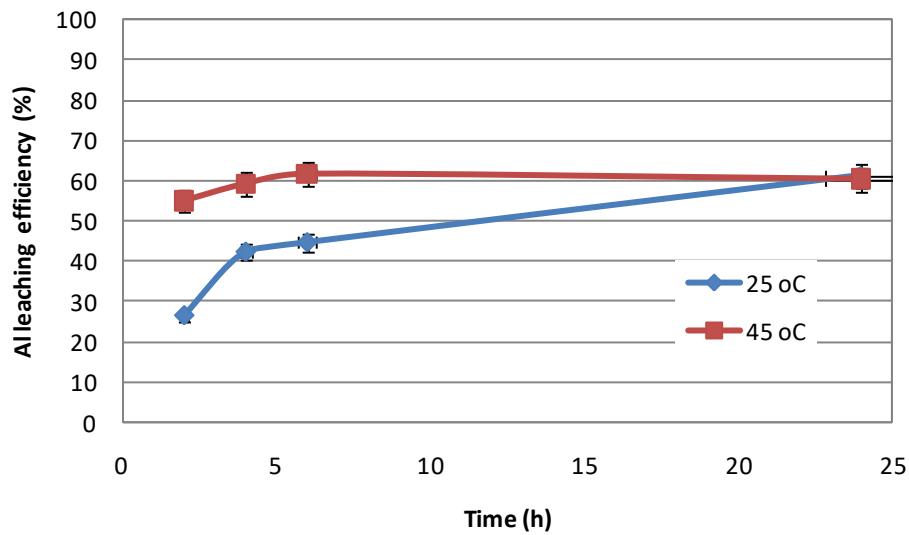


Figure. S4. The effect of temperature on Al leaching (m-Si panel, HNO_3 2N, S/L=1/10).

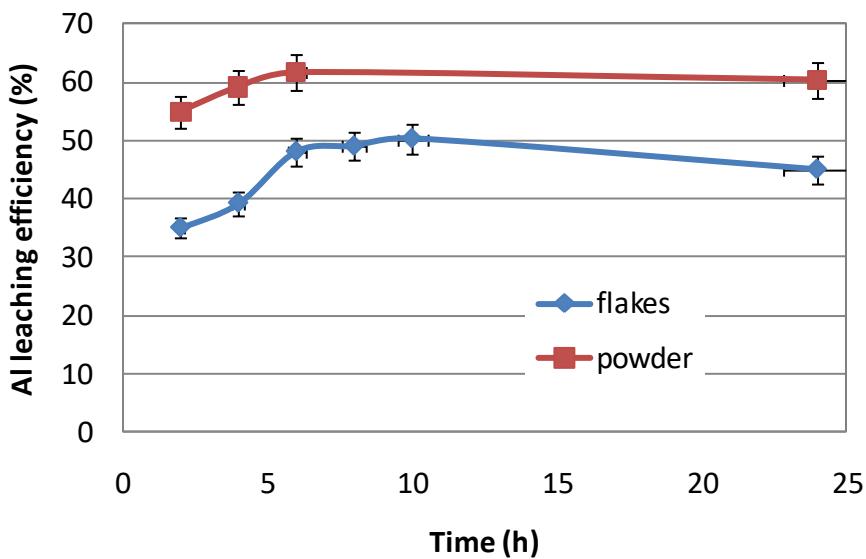


Figure. S5. The effect of milling on Al leaching (m-S panel, HNO_3 2N, S/L=1/10, 45 °C).